IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) A charged-particle beam writer which draws a pattern on a specimen with a charged-particle beam generated from a single particle generator by both of a VSB (variable-shaped beam) strategy and a ~~mask scan strategy~~ scan-projection strategy, the charged-particle beam writer comprising:

a data creating unit configured to create pattern data by combining first figure data and decompressed second figure data, said pattern data representing a state where a first figure defined by the first figure data and drawn by the VSB strategy and a second figure defined by the second figure data and drawn by the scan-projection strategy are arranged on the specimen;

a computing unit configured to calculate, on the basis of the pattern data, the amount of correction for correcting the drawing dimensions of the first figure on the specimen and the drawing dimensions of the second figure on the specimen; and

a control unit configured to control the dose of beam at each position on the specimen on the basis of the calculated amount of correction.

2. (Original) The charged-particle beam writer according to claim 1, wherein the control unit controls the irradiation time of the charged-particle beam for each position on the specimen.

3. (Original) The charged-particle beam writer according to claim 1, wherein

the particle generator generates as much a charged-particle beam as corresponds to the current supplied to the particle generator, and

the control unit controls the current density of the supplied current for each position on the specimen.

4. (Original) The charged-particle beam writer according to claim 1, wherein the computing unit calculates the amount of correction on the basis of a pattern density distribution on the specimen.

5. (Currently Amended) The charged-particle beam writer according to claim 1, wherein the control unit, when there is a part of the specimen on which the first figure and the second figure overlap with each other, controls the dose of beam by the VSB strategy and the dose of beam by the ~~mask scan strategy~~ scan-projection strategy separately at the overlapping part.

6. (Currently Amended) The charged-particle beam writer according to claim 1, wherein the control unit, when multiple scanning is done by the ~~mask scan strategy~~ scan-projection strategy, controls the dose of beam based on the number of multiple scannings at each position on the specimen.

7. (Original) The charged-particle beam writer according to claim 1, further comprising:

a first shaping aperture with a rectangular aperture; and

a second shaping aperture with a polygonal aperture and a plurality of character apertures, wherein

a variable-shaped beam is formed by an optical overlap between the rectangular aperture and the polygonal aperture and a character beam is formed by selecting one of the character apertures.

8. (Currently Amended) The charged-particle beam writer according to claim 1, wherein a part of the second figure is scanned by the ~~mask-scan strategy~~ scan-projection strategy.

9. (Currently Amended) A charged-particle beam writer which transfers character patterns onto a specimen by a ~~mask-scan strategy~~ scan-projection strategy for scanning the patterns on a mask with a charge-particle beam, the charged-particle beam writer comprising:

a data creating unit configured to create pattern data representing a state where the character patterns are arranged on the specimen;

a computing unit configured to calculate, on the basis of the pattern data, the amount of correction for correcting the drawing dimensions of the character patterns on the specimen; and

a control unit configured to control the dose of beam at each position on the specimen on the basis of the calculated amount of correction.